## 1. General description

PNP low  $V_{\text{CEsat}}$  Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

NPN complement: PBSS4330PA.

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

## 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	-	75	107	mΩ



30 V, 3 A PNP low VCEsat (BISS) transistor

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	Е	emitter		1—
3	С	collector	Transparent top view DFN2020-3 (SOT1061)	2 sym013

# 6. Ordering information

Table 3. Ordering information

Type number	Package	ge				
	Name	Description	Version			
PBSS5330PA	DFN2020-3	DFN2020-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5330PA	AJ

30 V, 3 A PNP low VCEsat (BISS) transistor

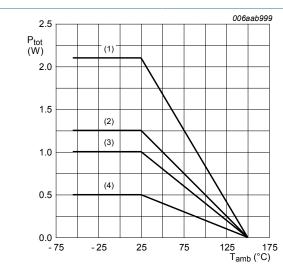
# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
$V_{CEO}$	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-5	Α
I <sub>B</sub>	base current			-	-500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.25	W
			[4]	-	2.1	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (4) FR4 PCB, standard footprint

#### Fig. 1. Power derating curves

PBSS5330PA

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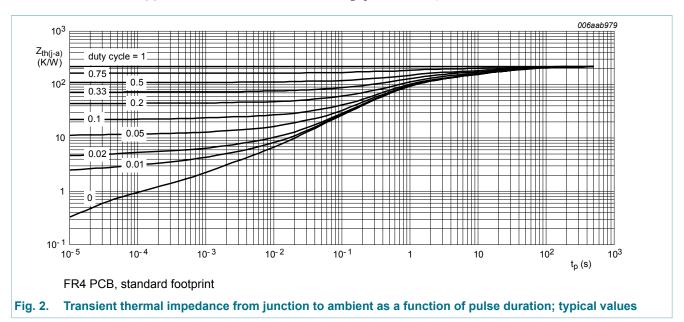
30 V, 3 A PNP low VCEsat (BISS) transistor

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance		[1]	-	-	250	K/W
from junction ambient	from junction to		[2]	-	-	125	K/W
	ambient		[3]	-	-	100	K/W
			[4]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



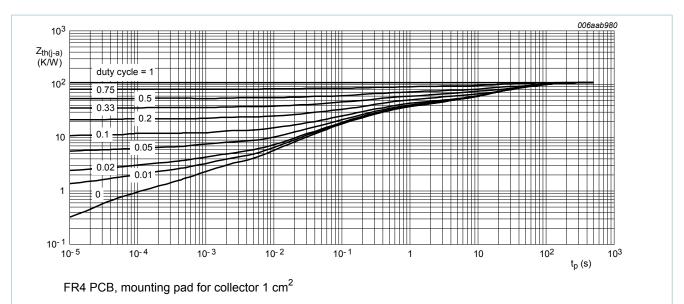


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

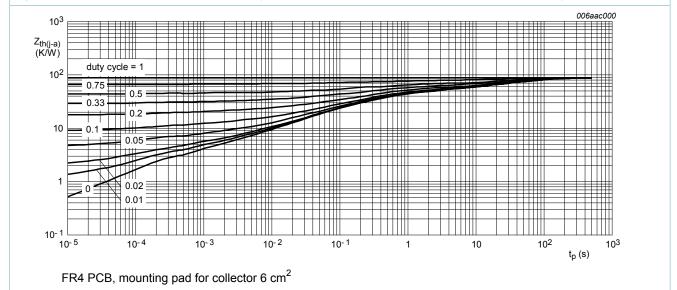
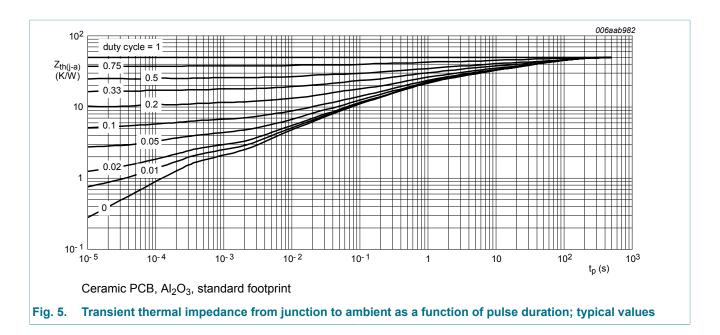


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



30 V, 3 A PNP low VCEsat (BISS) transistor

# 10. Characteristics

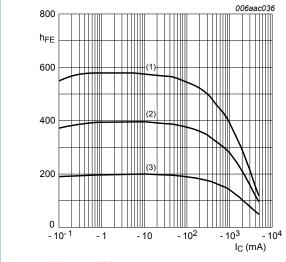
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -24 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V; } I_{C} = -0.5 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 ^{\circ}\text{C}$	200	320	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02 \text{ ; } T_{amb}$ = 25 °C	175	280	450	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02 \text{ ; } T_{amb}$ = 25 °C	140	210	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -3 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	100	160	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -0.5 A; $I_B$ = -50 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02 \text{ ; } T_{amb}$ = 25 °C	-	-45	-70	mV
		$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-90	-130	mV
		$I_C$ = -2 A; $I_B$ = -100 mA; pulsed; $t_p \le 300 \text{ μs}$ ; $\delta \le 0.02 \text{ ; } T_{amb}$ = 25 °C	-	-170	-240	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed;	-	-230	-320	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$t_p \le 300 \text{ μs}; \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	-	75	107	mΩ
$V_{BEsat}$	base-emitter saturation voltage	$I_{C}$ = -2 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}C$	-	-0.89	-1.1	V
		$I_{C}$ = -3 A; $I_{B}$ = -300 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 ^{\circ}C$	-	-0.97	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02 \text{ ; } T_{amb}$ = 25 °C	-	-0.75	-1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -9 V; I <sub>C</sub> = -2 A; I <sub>Bon</sub> = -0.1 A;	-	11	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 0.1 A; T <sub>amb</sub> = 25 °C	-	59	-	ns
t <sub>on</sub>	turn-on time		-	70	-	ns
t <sub>s</sub>	storage time		-	165	-	ns
t <sub>f</sub>	fall time		-	35	-	ns
t <sub>off</sub>	turn-off time		-	200	_	ns

PBSS5330PA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	165	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_E$ = 0 A; $i_e$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C	-	38	45	pF



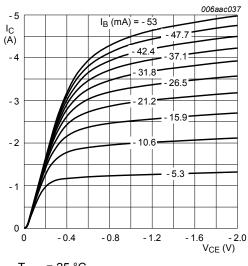
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

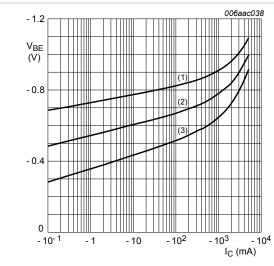
(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 6. DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 7. Collector current as a function of collectoremitter voltage; typical values



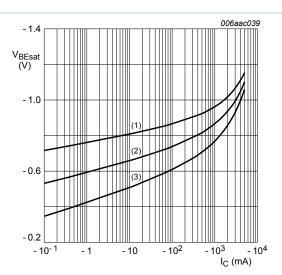
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter voltage as a function of collector current; typical values



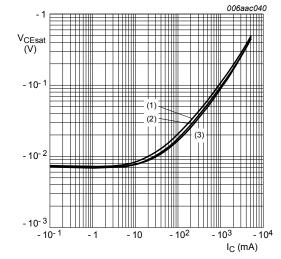
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values



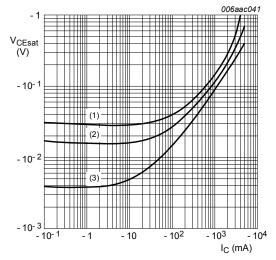
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

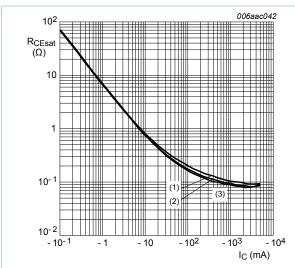


(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



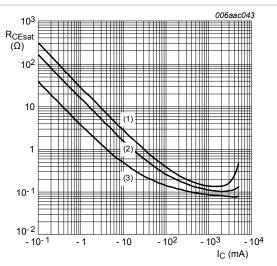
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values

30 V, 3 A PNP low VCEsat (BISS) transistor

# 11. Test information

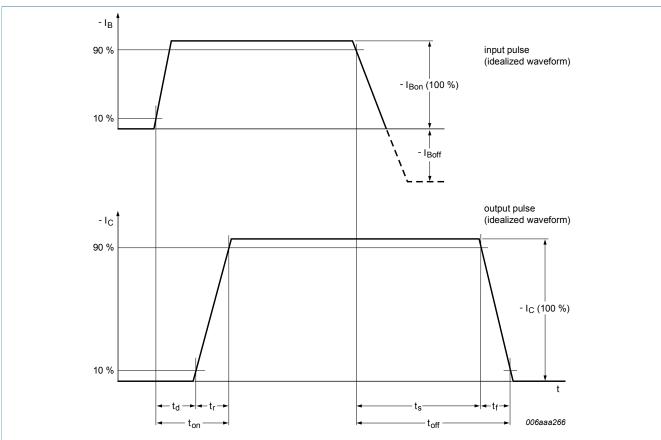


Fig. 14. BISS transistor switching time definition

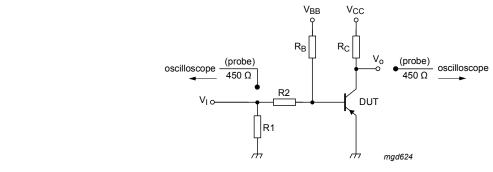
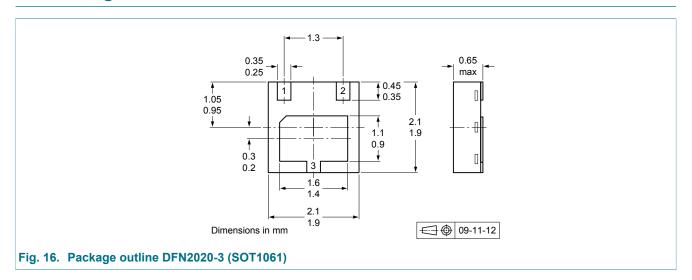


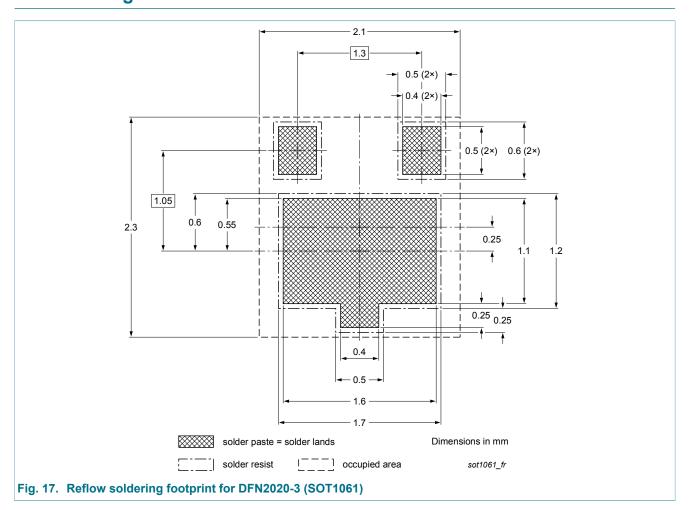
Fig. 15. Test circuit for switching times

30 V, 3 A PNP low VCEsat (BISS) transistor

# 12. Package outline



# 13. Soldering



30 V, 3 A PNP low VCEsat (BISS) transistor

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5330PA v.2	20150407	Product data sheet	-	PBSS5330PA v.1		
Modifications:	<ul> <li>Condition V<sub>CE</sub> changed for parameter I<sub>CES</sub> in Table 7, Characteristics</li> </ul>					
PBSS5330PA v.1	20100419	Product data sheet	-	-		

#### 30 V, 3 A PNP low VCEsat (BISS) transistor

## 15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### 30 V, 3 A PNP low VCEsat (BISS) transistor

## 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	7
11	Test information	11
12	Package outline	12
13	Soldering	12
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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